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(54) **Title:** FIELD EFFECT TRANSISTOR (FET) DEVICES

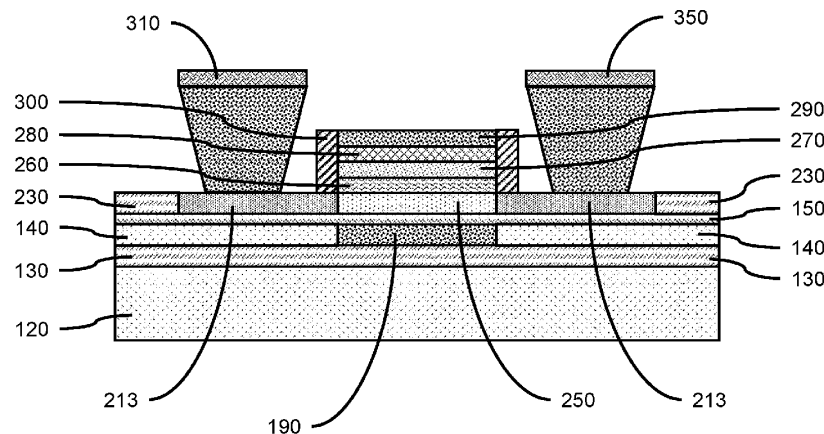


FIG. 7

(57) **Abstract:** A field effect transistor (FET) device is provided. The device includes an isolation region on a support substrate that separates a first back gate from a second back gate, and a gate dielectric layer on a first channel region and a second channel region. The device further includes a conductive gate layer having a work function value and a ferroelectric layer on the gate dielectric layer, wherein the first back gate can adjust a threshold voltage for the first channel region, and the second back gate can adjust a threshold voltage for the second channel region.

[Continued on next page]



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